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Data Sheet

November 2013

30 A, 1200 V, Hyperfast Diode

The RHRP30120 is a hyperfast diode with soft recovery characteristics. It has the half recovery time of ultrafast diodes and is silicon nitride passivated ionimplanted epitaxial planar construction. These devices are intended to be used as freewheeling/ clamping diodes and diodes in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Ordering Information

PART NUMBER	PACKAGE	BRAND	
RHRP30120	TO-220AC	RHR30120	

NOTE: When ordering, use the entire part number.

Symbol



Features

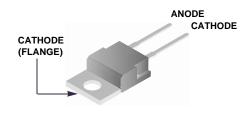
- Hyperfast Recovery t_{rr} = 85 ns (@ I_F = 30 A)
- Max Forward Voltage, V_F = 3.2 V (@ T_C = 25°C)
- 1200 V Reverse Voltage and High Reliability
- · Avalanche Energy Rated
- RoHS Compliant

Applications

- Switching Power Supplies
- · Power Switching Circuits
- · General Purpose

Packaging

JEDEC TO-220AC



Absolute Maximum Ratings T _C = 25 °C		
	RHRP30120	UNIT
Peak Repetitive Reverse VoltageVRRM	1200	V
Working Peak Reverse Voltage	1200	V
DC Blocking Voltage	1200	V
Average Rectified Forward Current	30	Α
$(T_C = 78^{\circ}C)$		
Repetitive Peak Surge Current	60	Α
(Square Wave, 20 kHz)		
Nonrepetitive Peak Surge Current	300	Α
(Halfwave, 1 Phase, 60 Hz)		
Maximum Power Dissipation	125	W
Avalanche Energy (See Figures 7 and 8)	30	mJ
Operating and Storage Temperature	-65 to 175	oC

Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
V _F	I _F = 30 A	-	-	3.2	V
	I _F = 30 A, T _C = 150 °C	-	-	2.6	V
I _R	V _R = 1200 V	-	-	250	μΑ
	V _R = 1200 V, T _C = 150 °C	-	-	1	mA
t _{rr}	$I_F = 1 A$, $d i_F/dt = 100 A/\mu s$	-	-	65	ns
	$I_F = 3.0$ A , d i $_F/dt = 100$ A/ μs	-	-	85	ns
t _a	$I_F = 3.0$ A , d i $_F/dt = 100$ A/ μs	-	48	-	ns
t _b	$I_F = 3.0$ A , d i $_F/dt = 100$ A/ μs	-	22	-	ns
R _θ JC		-	-	1.2	°C/W

DEFINITIONS

 V_F = Instantaneous forward voltage (pw = 300 μ s, D = 2%).

I_R = Instantaneous reverse current.

 T_{rr} = Reverse recovery time (See Figure 6), summation of t_a + t_b .

 t_a = Time to reach peak reverse current (See Figure 6).

 t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 6).

 $R_{\theta JC}$ = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

Typical Performance Curves

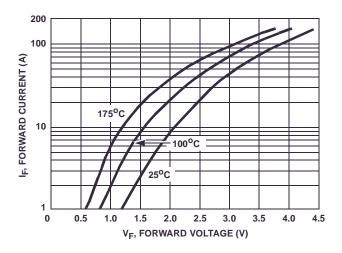


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

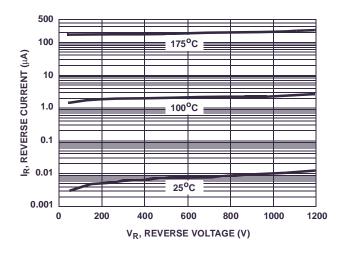


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

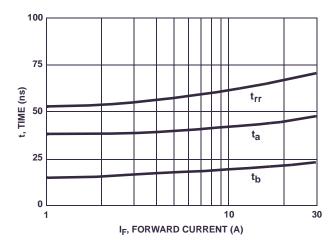


FIGURE 3. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT

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FIGURE 4. CURRENT DERATING CURVE

Test Circuits and Waveforms

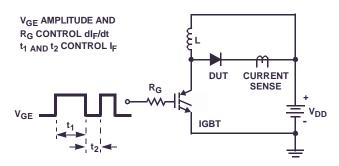


FIGURE 5. t_{rr} TEST CIRCUIT

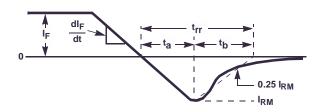


FIGURE 6. t_{rr} WAVEFORMS AND DEFINITIONS

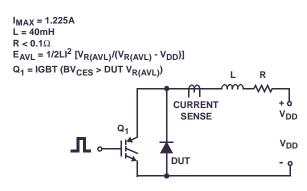


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

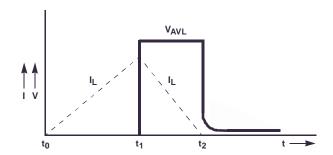


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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